

CLAIMS

We claim:

1. A method in a computing system for controlling an electroplating process in which a sequence of workpieces are electroplated with a material each in an electroplating cycle, such controlling including designating, for each electroplated workpiece, currents supplied to each of a plurality of electroplating anodes, comprising:

constructing a Jacobian sensitivity matrix characterizing the effects on plated material thickness at each of a plurality of workpiece positions of varying the currents supplied each of the plurality of anodes;

receiving a specification of target plating material thickness at each of the plurality of workpiece positions;

applying the Jacobian sensitivity matrix to make a first determination of how a baseline set of anode currents should be varied to produce the specified target plating material thicknesses rather than baseline plating material thicknesses indicated to result from the baseline set of anode currents;

generating an indication to conduct a first electroplating cycle with respect to a first workpiece using a designated set of anode currents produced by varying the baseline set of anode currents in accordance with the first determination;

receiving measured plating material thicknesses thickness at each of the plurality of workpiece positions of the first workpiece;

applying the Jacobian sensitivity matrix to make a second determination of how the set of anode currents designated for the first electroplating cycle should be varied to produce the specified target plating material thicknesses rather than measured plating material thicknesses of the first workpiece; and

generating an indication to conduct a second electroplating cycle with respect to a second workpiece using a designated set of anode currents produced by

varying the set of anode currents designated for the first electroplating cycle in accordance with the second determination.

2. The method of claim 1, further comprising:

receiving measured plating material thicknesses at each of the plurality of workpiece positions from the second electroplating cycle;

determining that the measured plating material thicknesses from the second electroplating cycle are within a specified tolerance of the specified target plating material thicknesses; and

in response to the determination, generating one or more indications to conduct a plurality of further electroplating cycles using the set of anode currents designated for the second electroplating cycle.

3. The method of claim 1, further comprising:

receiving measured plating material thicknesses at each of the plurality of workpiece positions from the second electroplating cycle;

applying the Jacobian sensitivity matrix to make a third determination of how the set of anode currents designated for the second electroplating cycle should be varied to produce the specified target plating material thicknesses rather than measured plating material thicknesses of the second workpiece; and

generating an indication to conduct a third electroplating cycle using a designated set of anode currents produced by varying the set of anode currents designated for the second electroplating cycle in accordance with the second determination.

4. The method of claim 1, further comprising:

before the first electroplating cycle, receiving measured seed layer thicknesses of the first workpiece at each of the plurality of workpiece positions; and

before the second electroplating cycle, receiving measured seed layer thicknesses of the second workpiece at each of the plurality of workpiece positions, and wherein the second determination made by applying the Jacobian sensitivity matrix is a determination of how the set of anode currents designated for the first electroplating cycle should be varied to produce the specified target plating material thicknesses rather than measured plating material thicknesses of the first workpiece in light of the differences between the measured seed layer thicknesses of the first and second workpieces.

5. The method of claim 1 wherein the Jacobian sensitivity matrix is generated from a mathematical model of the electroplating process.

6. The method of claim 1 wherein the Jacobian sensitivity matrix is generated from data obtained by operating the electroplating process.

7. The method of claim 1 wherein the baseline plating material thicknesses are generated from data obtained by simulating operation of the electroplating process using a mathematical model of the electroplating process, the simulation using the baseline anode currents.

8. The method of claim 1 wherein the baseline plating material thicknesses are generated from data obtained by operating the electroplating process with the baseline anode currents.

9. A method in a computing system for providing closed-loop control of a process for applying a coating material to a series of workpieces to produce a coating layer of the coating material, comprising:

(a) receiving a coating profile specifying one or more attributes of the coating layer to be produced on the workpieces;

(b) designating a first set of coating parameters for use in coating a first workpiece;

(c) identifying a first set of discrepancies between attributes of the coating layer produced on the first workpiece using the first set of coating parameters and the attributes specified by the coating profile;

(d) determining a first set of modifications to the first set of coating parameters expected to reduce the identified first set of discrepancies;

(e) modifying the first set of coating parameters in accordance with the determined first set of modifications to produce a second set of coating parameters;

(f) designating the second set of coating parameters for use in coating a second workpiece; and

(g) repeating (c) – (f) for subsequent workpieces in the series until the identified set of discrepancies falls within a selected tolerance.

10. The method of claim 9, further comprising, after (g), designating the most recently-produced set of coating parameters for use in coating subsequent workpieces.

11. The method of claim 9 wherein each workpiece is a silicon wafer.

12. The method of claim 9 wherein the coating material is a conductor.

13. The method of claim 9 wherein the coating material is copper.

14. The method of claim 9 wherein the process is performed in an electrolysis chamber having a plurality of anodes, and wherein at least a portion of

the coating parameters are currents to transmit through identified anodes among the plurality of anodes.

15. The method of claim 9 wherein at least a portion of the attributes of the coating layer to be produced on the workpieces specified by the coating profile are target thicknesses of the coating layer in selected regions on the workpiece.

16. The method of claim 15 wherein the discrepancies identified in (c) correspond to differences between thicknesses measured in the selected regions on the coated workpiece and the target thicknesses specified by the coating profile for the selected regions on the workpiece.

17. The method of claim 15, further comprising:

generating a set of predicted coating thicknesses in the selected regions on the first workpiece based upon the first set of coating parameters;

receiving an indication of thicknesses measured in the selected regions on the coated first workpiece;

computing a difference between the predicted coating thicknesses and the indicated measured thicknesses; and

subtracting the computed difference from the determined first set of modifications before using the first set of modifications to modify the first set of coating parameters.

18. The method of claim 15 wherein each of the workpieces bears a seed layer,

the method further comprising:

for each the first and second workpieces, receiving an indication of seed layer thicknesses measured in the selected regions on the workpiece before the workpiece is coated; and

before designating the second set of coating parameters for use in coating a second workpiece, further adjusting the second set of coating parameters in to adjust for differences between the measured thicknesses of the first and second workpieces.

19. The method of claim 9 wherein the coating process is electrolytic deposition.

20. The method of claim 9 wherein the coating process is electrophoretic deposition.

21. The method of claim 9 wherein the coating process is chemical vapor deposition.

22. The method of claim 9 wherein the coating process is physical vapor deposition.

23. The method of claim 9 wherein the coating process is electron beam atomization.

24. The method of claim 9 wherein (d) utilizes a sensitivity matrix mapping changes in attributes to changes in coating parameters expected to produce those attribute changes.

25. A computer-readable medium whose contents cause a computing system to provide closed-loop control of a process for applying a coating material to a series of workpieces to produce a coating layer of the coating material by:

(a) receiving a coating profile specifying one or more attributes of the coating layer to be produced on the workpieces;

(b) designating a first set of coating parameters for use in coating a first workpiece;

(c) identifying a first set of discrepancies between attributes of the coating layer produced on the first workpiece using the first set of coating parameters and the attributes specified by the coating profile;

(d) determining a first set of modifications to the first set of coating parameters expected to reduce the identified first set of discrepancies;

(e) modifying the first set of coating parameters in accordance with the determined first set of modifications to produce a second set of coating parameters; and

(f) designating the second set of coating parameters for use in coating a second workpiece.

26. The computer-readable medium of claim 25, further comprising repeating (c) – (f) for subsequent workpieces in the series until the identified set of discrepancies falls within a selected tolerance.

27. A method in a computing system for automatically configuring parameters controlling operation of a deposition chamber to deposit material on each of a sequence of at least two wafers to improve conformity with a specified deposition pattern, comprising:

for each of the sequence of wafers, measuring thicknesses of the wafer before material is deposited on the wafer;

for each of the sequence of wafers, measuring thicknesses of the wafer after material is deposited on the wafer;

for each of the sequence of wafers after the first wafer of the sequence, configuring the parameters for depositing material on the wafer based on the specified deposition pattern, the measured thickness of the current wafer before material is deposited on the current wafer, the measured thickness of the previous wafer in the sequence before material is deposited on the previous wafer, the

parameters used for depositing material on the previous wafer, and the measured thicknesses of the previous wafer after material is deposited on the previous wafer.

28. The method of claim 27 wherein the specified deposition pattern is a flat deposition pattern.

29. The method of claim 27 wherein the specified deposition pattern is a concave deposition pattern.

30. The method of claim 27 wherein the specified deposition pattern is a convex deposition pattern.

31. The method of claim 27 wherein the specified deposition pattern is an arbitrary radial profile.

32. The method of claim 27 wherein the specified deposition pattern is an arbitrary profile.

33. The method of claim 27, further comprising, for a second deposition chamber:

retrieving a set of offset values characterizing differences between the deposition chamber and the second deposition chamber;

modifying the parameters most recently configured for the deposition chamber in accordance with the retrieved set of offset values to obtain a parameters for the second deposition chamber; and

configuring the second deposition chamber with the obtained parameters for the second deposition chamber.

34. An apparatus for automatically configuring parameters controlling operation of a deposition chamber to deposit material on each of a

sequence of wafers to improve conformity with a specified deposition pattern, comprising:

- a pre-deposition measuring subsystem that measures thicknesses of each of the sequence of wafers before material is deposited on the wafer;

- a post-deposition measuring subsystem that measures thicknesses of each of the sequence of wafers after material is deposited on the wafer;

- a parameter configuration subsystem that configures the parameters for depositing material on each of the sequence of wafers after the first wafer of the sequence based on the specified deposition pattern, the measured thickness of the current wafer before material is deposited on the current wafer, the measured thickness of the previous wafer in the sequence before material is deposited on the previous wafer, the parameters used for depositing material on the previous wafer, and the measured thicknesses of the previous wafer after material is deposited on the previous wafer.

35. A method in a computing system for constructing a sensitivity matrix usable to adjust currents for a plurality of electrodes in an electroplating chamber to improve plating uniformity, comprising:

- for each of a plurality of radii on the plating workpiece, obtaining a plating thickness on the workpiece at that radius when a set of baseline currents are delivered through the electrodes;

- for each of the electrodes, for each of a plurality of plating workpiece radii, obtaining a plating thickness on the workpiece at that radius when the baseline currents are perturbed for that electrode; and

- constructing a matrix, a first dimension of the matrix corresponding to the plurality of electrodes, a second dimension of the matrix corresponding to the plurality of radii, each entry for a particular electrode and a particular radius being determined by subtracting the thickness at that radius when the baseline currents are delivered through the electrodes from the thickness at that radius when the baseline

currents are perturbed for that electrode, then dividing by the magnitude by which that the current for that electrode was perturbed from its baseline current.

36. The method of claim 35 wherein the current for each electrode is perturbed by approximately +.05 amps.

37. The method of claim 35 wherein the current for each electrode is perturbed by a factor in the range between 1% and 10%.

38. The method of claim 35 wherein the obtained thicknesses are obtained by executing a simulation of the operation of the electroplating chamber based upon a mathematical model of the electroplating chamber.

39. The method of claim 35 wherein the obtained thicknesses are obtained by measuring workpieces plated in the electroplating chamber.

40. The method of claim 35, further comprising repeating the method to produce additional sensitivity matrices for a variety of different conditions.

41. The method of claim 35, further comprising using the constructed sensitivity matrix to modify for use in plating a second workpiece currents used to plate a first workpiece, such that the modified currents cause the second workpiece to be plated more uniformly than the first workpiece.

42. One or more computer memories collectively containing a sensitivity matrix data structure relating to a deposition chamber having a plurality of deposition initiators for depositing material on a workpiece having selected radii, a control parameter being associated with each of the deposition initiators, the data structure comprising a plurality of quantitative entries, each of the entries

predicting, for a given change in the control parameter associated with a given deposition initiator, the expected change in deposited material thickness at a given radius,

such that the contents of the data structure may be used to determine revised deposition initiator parameters for better conforming deposited material thicknesses to a target profile for deposited material thicknesses.

43. The computer memories of claim 42 wherein the deposition initiators are electrodes, and wherein the control parameters associated with the deposition initiators are currents delivered through the electrodes.

44. The computer memories of claim 42 wherein the sensitivity matrix data structure is a Jacobian sensitivity matrix.

45. The computer memories of claim 42 wherein the computer memories contain multiple sensitivity matrix data structures, each adapted to a different set of conditions.

46. One or more computer memories collectively containing a data structure for controlling a material deposition process, comprising a set of parameter values used in the material deposition process, the parameters having been generated by adjusting an earlier-used set of parameters to resolve differences between measurements of a workpiece deposited using the earlier-used set of parameters and a target deposition profile specified for the deposition process,

such that the contents of the data structure may be used to deposit an additional workpiece in greater conformance with the specified deposition profile.

47. The computer memories of claim 46 wherein the deposition process utilizes a plurality of electrodes, and wherein each parameter value of the set is an amount of current to be delivered through one of the plurality of electrodes.

48. One or more computer memories collectively containing a deposition chamber offset data structure, comprising a set of values indicating how to adjust a first parameter set used to obtain acceptable deposition results in a first deposition chamber to produce a second parameter set usable to obtain acceptable deposition results in a second deposition chamber.

49. A reactor for electrochemically processing a microelectronic workpiece comprising:

- a fluid chamber configured to contain an electrochemical processing fluid;

- a plurality of electrodes in the fluid chamber;

- a workpiece holder positionable to hold the microelectronic workpiece in the fluid chamber;

- an electrical power supply connected to the surface of the microelectronic workpiece and to the plurality of electrodes, at least two of the plurality of electrodes being independently connected to the electrical power supply to facilitate independent supply of power thereto; and

- a control system connected to the electrical power supply to control at least one electrical power parameter respectively associated with each of the independently connected electrodes, the control system setting the at least one electrical power parameter for a given one of the independently connected electrodes based on one or more inputted parameters and a plurality of predetermined sensitivity values, the predetermined sensitivity values corresponding to process perturbations resulting from perturbations of the electrical power parameter for the given one of the independently connected electrodes.

50. The reactor of claim 49 wherein the at least one electrical parameter is electrical current.

51. The reactor of claim 49 wherein the sensitivity values are logically arranged within the control system as one or more Jacobian matrices.

52. The reactor of claim 49 wherein the at least one user input parameter comprises the thickness of a film that is to be electrochemically deposited on the at least one surface of the microelectronic workpiece.

53. The reactor of claim 49 wherein the independently connected electrodes are arranged concentrically with respect to one another.

54. The reactor of claim 49 wherein the independently connected electrodes are disposed at the same effective distance from the microelectronic workpiece.

55. The reactor of claim 54 wherein the independently connected electrodes are arranged concentrically with respect to one another.

56. The reactor of claim 49 wherein at least two of the independently connected electrodes are disposed at different effective distances from the surface of the microelectronic workpiece.

57. The reactor of claim 56 wherein the independently connected electrodes are arranged concentrically with respect to one another.

58. The reactor of claim 57 wherein the independently connected electrodes are arranged at increasing distances from the microelectronic workpiece from an outermost one of the plurality of concentric anodes to an innermost one of the independently connected electrodes.

59. The reactor of claim 49 wherein one or more of the independently connected electrodes is a virtual electrode.

60. A method in a computing system for controlling an electroplating process having multiple steps in an electroplating chamber having a plurality of electrodes, comprising:

for each electrode, determining the net plating charge delivered through the electrode during a first plating cycle to plate a first workpiece by summing the plating charges delivered through the electrode in each step of the process;

comparing a plating profile achieved in plating the first workpiece to a target plating profile to identify deviations between the achieved plating profile and the target plating profile;

determining new net plating charges for each electrode selected to reduce the identified deviations in a second workpiece;

for each new plating charge, distributing the new net plating charge across the steps of the process;

using the distributed new net plating charges to determine a current for each electrode for each step of the process; and

conducting a second plating cycle to plate a second workpiece, using the currents determined for each electrode for each step.

61. The method of claim 60 wherein the new net plating charges are distributed uniformly across all of the steps of the process.

62. The method of claim 60 wherein the new net plating charges are distributed across the steps of the process by distributing differences between the new net plating charge and the delivered net plating charge to a single step of the process.

63. The method of claim 60 wherein the distributing includes distributing the new net plating charges to each of two or more phases of a selected one of the steps of the process.

64. The method of step 60, further comprising repeating the method to further reduce deviations between the achieved plating profile and the target plating profile.

65. The method of step 60 wherein a sensitivity matrix is used to determine the new net plating charges.

66. The method of step 60 wherein a different sensitivity matrix is used to determine a new net plating charge for each step of the process.

67. A method in a computer system for evaluating a design for an electroplating reactor, comprising:

applying to a set of initial electrode currents a mathematical model embodying the reactor design to determine a first resulting plating profile;

comparing the first resulting plating profile to a target plating profile to obtain a first difference;

applying a sensitivity technique to identify a set of revised electrode currents;

applying the mathematical model to the set of revised electrode currents to determine a second resulting plating profile;

comparing the second resulting plating profile to the target plating profile to obtain a second difference; and

evaluating the design based on the obtained second difference.

68. An apparatus for automatically selecting parameters for using in controlling operation of a deposition chamber to deposit material on a selected wafer to optimize conformity with a specified deposition pattern, comprising:

a measurement receiving subsystem that receives:

pre-deposition thicknesses of the selected wafer before material is deposited on the wafer;

post-deposition thicknesses of an already-deposited wafer after material is deposited on the already-deposited wafer; and

pre-deposition thicknesses of the already-deposited wafer before material is deposited on the wafer; and

a parameter selection subsystem that selects the parameters to be used to deposit material on the selected wafer based on the specified deposition pattern, the pre-deposition thicknesses of the selected wafer, the pre-deposition thicknesses of the already-deposited wafer, parameters used for depositing material on the already-deposited wafer, and the post-deposition thicknesses of the already-deposited wafer.

69. The apparatus of claim 68, further comprising a deposition chamber for depositing material on the selected wafer using the parameters selected by the parameter selection subsystem.

70. The apparatus of claim 68, further comprising a memory containing a sensitivity matrix used by the parameter selection subsystem in selecting parameters to be used to deposit material on the selected wafer.

71. A method in a computing system for automatically configuring parameters usable to control operation of a deposition chamber to deposit material on a selected wafer to optimize conformity with a specified deposition pattern, comprising:

- receiving pre-deposition thicknesses of the selected wafer before material is deposited on the wafer;

- receiving post-deposition thicknesses of an already-deposited wafer after material is deposited on the already-deposited wafer; and

- receiving pre-deposition thicknesses of the already-deposited wafer before material is deposited on the wafer;

- selecting the parameters to be used to deposit material on the selected wafer based on the specified deposition pattern, the pre-deposition thicknesses of the selected wafer, the pre-deposition thicknesses of the already-deposited wafer, parameters used for depositing material on the already-deposited wafer, and the post-deposition thicknesses of the already-deposited wafer.

72. The method of claim 71, further comprising controlling a deposition chamber to deposit material on the selected wafer using the selected parameters.

73. The method of claim 71 wherein a sensitivity matrix is used in selecting parameters to be used to deposit material on the selected wafer.

74. A reactor for electrochemically processing a microelectronic workpiece comprising:

- a fluid chamber configured to contain an electrochemical processing fluid;

- a plurality of electrodes in the fluid chamber;

- a workpiece holder positionable to hold the microelectronic workpiece in the fluid chamber; and

an electrical power supply connected to the surface of the microelectronic workpiece and to the plurality of electrodes, at least two of the plurality of electrodes being independently connected to the electrical power supply to facilitate independent supply of power thereto, the power supply configured to provide power to each independently connected electrode in accordance with an electrical power parameter provided for the independently connected electrode, each electrical power parameter being based on one or more inputted parameters and a plurality of predetermined sensitivity values, the predetermined sensitivity values corresponding to process perturbations resulting from perturbations of the electrical power parameter for the given one of the independently connected electrodes.

75. The reactor of claim 74 wherein each electrical power parameter is a current level.

76. The reactor of claim 74, further comprising an electrical power parameter selection subsystem that selects the electrical power parameter corresponding to each independently connected electrode.

77. An method for electroplating a selected surface using a plurality of electrodes, comprising:

obtaining a current specification set comprised of a plurality of current levels each specified for a particular one of the plurality of electrodes, the current levels of the current specification set comprising a modification of current levels of a distinguished current specification set in order to improve results produced by electroplating in accordance with the distinguished current specification set; and

for each electrode, delivering the current level specified for the electrode by the current specification set to the electrode in order to electroplate the selected surface.

78. The method of claim 77 wherein the current specification set is obtained by receiving it via an interface.

79. The method of claim 78 wherein the interface is a user interface.

80. The method of claim 78 wherein the interface is a removable media drive.

81. The method of claim 78 wherein the interface is a network connection.

82. The method of claim 77 wherein the current specification set is obtained by modifying the distinguished current specification set.

83. A method for processing a microelectronic workpiece, comprising:

(a) applying a seed layer to the workpiece using a physical vapor deposition process;

(b) measuring non-uniformity of the applied seed layer using a metrology device;

(c) correcting the measured non-uniformity of the applied seed layer in an multiple-electrode reactor whose electrodes are operated in accordance with electrical parameters determined based on the measured non-uniformity of the applied seed layer and characteristics of the multiple-electrode reactor.

84. The method of claim 83, further comprising, after (c):

(d) subjecting the workpiece to an electroless ion plating process in order to enhance the seed layer.

85. The method of claim 84, further comprising, after (d):
measuring the thickness of the enhanced seed layer using a metrology device; and

depositing a bulk metal layer atop the seed layer in an multiple-electrode reactor whose electrodes are operated in accordance with electrical parameters determined based on the measured thickness of the enhanced seed layer and characteristics of the multiple-electrode reactor.

86. A method for processing microelectronic workpieces, comprising:

(a) applying a seed layer to a first workpiece using a first physical vapor deposition tool;

(b) applying a seed layer to a second workpiece using a second physical vapor deposition tool;

(c) measuring non-uniformity of the seed layer applied to the first workpiece using a metrology device;

(d) measuring non-uniformity of the seed layer applied to the second workpiece using a metrology device;

(e) correcting the measured non-uniformity of the seed layer applied to the first workpiece in a first multiple-electrode reactor whose electrodes are operated in accordance with electrical parameters determined based on the measured non-uniformity of the seed layer applied to the first workpiece and characteristics of the first multiple-electrode reactor

(f) correcting the measured non-uniformity of the seed layer applied to the second workpiece in a second multiple-electrode reactor whose electrodes are operated in accordance with electrical parameters determined based on the measured non-uniformity of the seed layer applied to the second workpiece and characteristics of the second multiple-electrode reactor.

87. The method of claim 86, further comprising, after (f):
measuring the thickness of the corrected seed layer of the first workpiece using a metrology device;

depositing a bulk metal layer atop the seed layer of the first workpiece in a third multiple-electrode reactor whose electrodes are operated in accordance with electrical parameters determined based on the measured thickness of the corrected seed layer of the first workpiece and characteristics of the third multiple-electrode reactor;

measuring the thickness of the corrected seed layer of the second workpiece using a metrology device;

depositing a bulk metal layer atop the seed layer of the second workpiece in a third multiple-electrode reactor whose electrodes are operated in accordance with electrical parameters determined based on the measured thickness of the corrected seed layer of the second workpiece and characteristics of the third multiple-electrode reactor.

88. A method for constructing a library of deposition process parameter sets for use in controlling a material deposition tool in which multiple control points are controlled in order to control material deposition, comprising:

receiving a plurality of recipes, each recipe identifying a different set of characteristics to be used in performing a deposition process with the tool;

for each received recipe,

operating the tool in accordance with the recipe, and controlling each of the control points in accordance with an initial parameter set, to deposit a test workpiece;

evaluating the deposited test workpiece;

identifying deviations between the evaluation of the deposited test workpiece and a target deposition profile;

modifying the initial parameter set in a manner projected to reduce the identified deviations; and

storing the modified initial parameter set in a manner that associates it with the received recipe.

89. The method of claim 88, further comprising:

selecting one of the plurality of recipes;

in response to the recipe selection, retrieving the parameter set associated with the selected recipe; and

operating the tool in accordance with the selected recipe, and controlling each of the control points in accordance with the retrieved parameter set, to deposit a workpiece.

90. The method of claim 88 wherein the control points of the deposition tool are electrodes, and wherein each initial and modified parameter set specifies a manner of controlling each of the electrodes.

91. One or more computer memories collectively containing a plurality of deposition process parameter sets for use in controlling a material deposition tool in which multiple control points are controlled in order to control material deposition, each parameter set being associated with a processing recipe and containing a parameters specifying how to control each of the control points when performing the processing recipe.

92. The computer memories of claim 91 wherein the parameter sets are determined experimentally under computer control.

93. A method for performing material deposition on a workpiece, comprising:

selecting one of a plurality of processing recipes;

in response to the recipe selection, from a plurality of deposition process parameter sets determined experimentally under computer control, retrieving a parameter set associated with the selected recipe; and

operating a deposition tool in accordance with the selected recipe, and controlling each of a plurality of control points of the tool in accordance with the retrieved parameter set, to deposit a workpiece.

94. One or more computer memories collectively containing an electroplating current data structure, the data structure comprising information specifying, for each of a plurality of seed layer resistivity ranges, a set of currents to be delivered to a group of electrodes in order to electroplate a workpiece having a seed layer whose resistivity falls within the range.

95. The computer memories of claim 94 wherein the sets of currents specified by information in the data structure are experimentally determined under computer control.

96. A method in a computing system for automatically configuring parameters usable to control operation of a reaction chamber to electropolish a selected wafer to optimize conformity with a specified electropolishing pattern, comprising:

receiving pre-polishing thicknesses of the selected wafer before the selected wafer is polished;

receiving post-polishing thicknesses of an already-polished wafer after the already-polished wafer is polished; and

receiving pre-polishing thicknesses of the already-polished wafer before the already-polished wafer is polished;

selecting the parameters to be used to polish the selected wafer based on the specified polishing pattern, the pre-polishing thicknesses of the selected wafer, the pre-polishing thicknesses of the already-polished wafer, parameters used

for polishing the already-polished wafer, and the post-polishing thicknesses of the already-polished wafer.

97. A method in a computing system for determining deposition parameters to use in performing material deposition on a workpiece, comprising:

receiving thickness measurements at predetermined locations on the workpiece;

receiving a deposition profile specifying the pattern in which material is to be deposited on the workpiece;

obtaining a starting set of deposition parameters, a starting set of pre-deposition thickness measurements, and a starting set of deposited thicknesses corresponding to the starting sets of deposition parameters and pre-deposition thickness measurements;

based upon the received and obtained information, determining a set of deposition parameters to use in performing material deposition on the workpiece.

98. The method of claim 97 wherein the set of deposition parameters to use in performing material deposition on the workpiece is determined using sensitivity techniques.

99. A method in a computing system for electroplating a microelectronic workpiece, comprising:

receiving data representing a profile of a seed layer that has been applied to the workpiece;

identifying deficiencies in the seed layer based upon the profile of the seed layer represented by the received data;

determining a set of control parameters for plating the workpiece in a manner that compensates for the identified deficiencies in the seed layer; and

communicating the determined set of control parameters to a plating tool for use in plating the workpiece.

100. The method of claim 99 wherein the determined set of control parameters is, for each of a plurality of electrodes of the plating tool, one or more current levels to be delivered through the electrode.